EE-07
www.oxfordplasma.de/process/inp_dfb.htm

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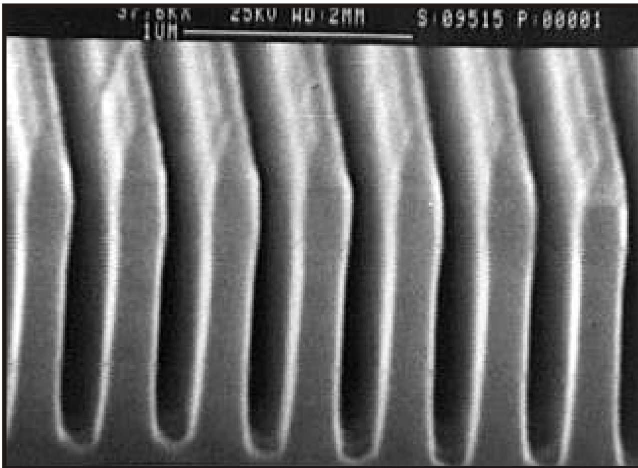
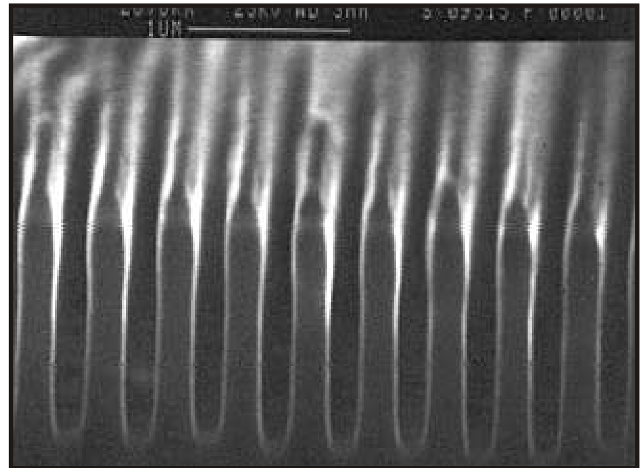
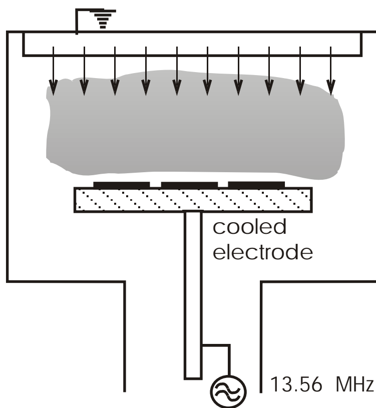
Plasmalab Data

CH_4 / H_2 - RIE: InP DFB Laser Etching







1.2 µm deep, anisotropic etch in InP with aspect ratio 5:1

Plasmalab 80 Plus

Plasmalab System 100

Plasmalab System 133

Technology:

Parallel-Plate reactor
Process gases: CH_4 / H_2
RIE Mode: 13.56 MHz

Results:

Rate : ca. 55 nm/ min
Mask: Photoresist or SiO_2
Profile: anisotropic
Aspect ratio: up to 7:1
Smooth Walls
Bottoms: very low roughness
Uniformity: $\pm$ 3% (3“ diam.)